

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP02515K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

• V_{DS} =250V,I_D =15A

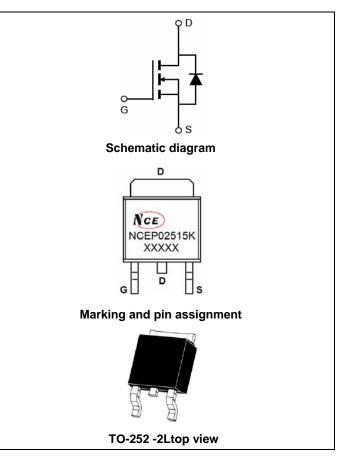
 $R_{DS(ON)}$ =200m Ω (typical) @ V_{GS} =10V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP02515K	NCEP02515K	TO-252-2L	1	-	-

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	250	V
Gate-Source Voltage	V _{GS}	±30	V
Drain Current-Continuous	I _D	15	Α
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	10.6	Α
Pulsed Drain Current	I _{DM}	60	А
Maximum Power Dissipation	P _D	140	W
Derating factor ^(Note 5)		0.93	W/°C
Avalanche Current (Note 1)	I _{AR}	15	Α
Single pulse avalanche energy (Note 5)	E _{AS}	80	mJ
Drain Source voltage slope, V _{DS} ≤200 V,	dv/dt	50	V/ns
Reverse diode dv/dt, V _{DS} ≤200 V, I _{SD} <i<sub>D</i<sub>	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}\!\mathbb{C}$

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NCEP02515K

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	R _{eJC}	1.1	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	250	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =250V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±30 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics	·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance (Note 6)	R _{DS(ON)}	V _{GS} =10V, I _D =7.5A	-	200	220	mΩ
Gate resistance	R _G		-	4.5	-	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =15A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ -425\/\/ -0\/	-	475		PF
Output Capacitance	Coss	V_{DS} =125V, V_{GS} =0V, F=1.0MHz	-	34		PF
Reverse Transfer Capacitance	C _{rss}	r-1.0IVIHZ	-	1.2		PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t _{d(on)}		-	4	-	nS
Turn-on Rise Time	t _r	V_{DD} =125V, RL=8 Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	10	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Qg	\/ -125\/ -15 \	-	8.9	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =125V, I_{D} =15A, V_{GS} =10V	-	3.3	-	nC
Gate-Drain Charge	Q _{gd}	VGS-1UV	-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =15A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	15	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = I_S$	-	25	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	110	-	nC

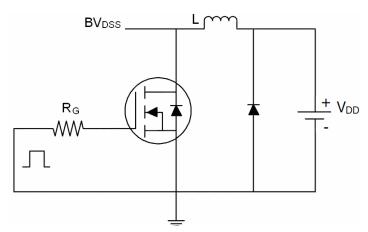
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω
- 6. Pulse Test: Pulse Width 200µs

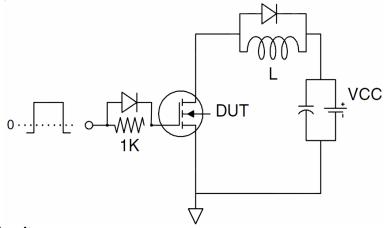


Test Circuit

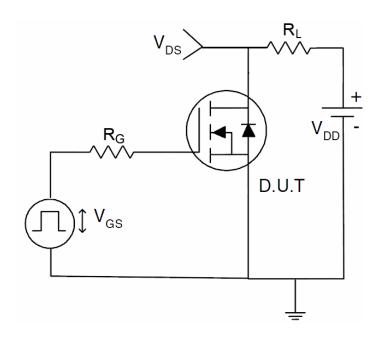
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

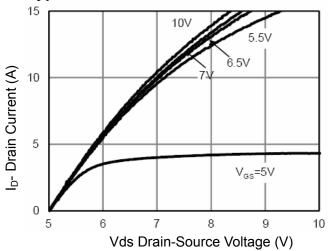


Figure 1 Output Characteristics

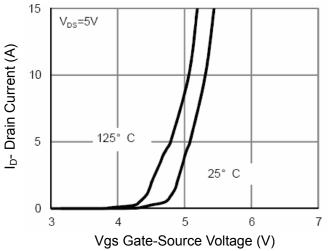


Figure 2 Transfer Characteristics

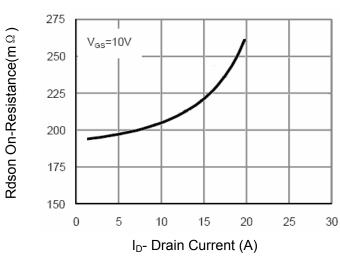


Figure 3 Rdson- Drain Current

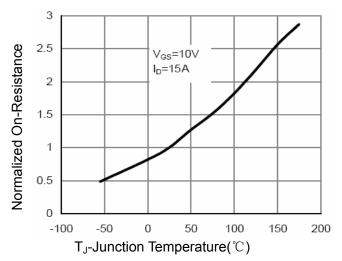


Figure 4 Rdson-Junction Temperature

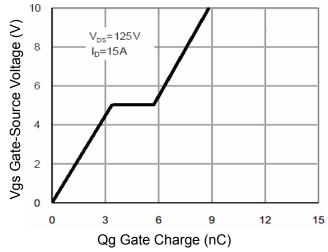


Figure 5 Gate Charge

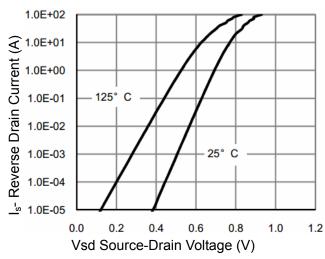


Figure 6 Source- Drain Diode Forward



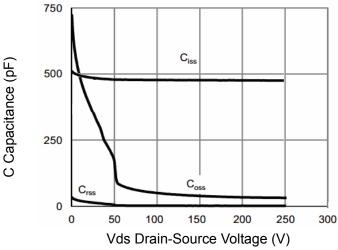


Figure 7 Capacitance vs Vds

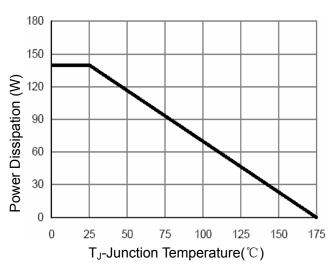


Figure 9 Power De-rating

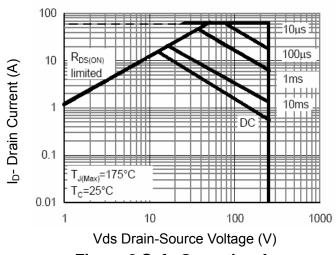


Figure 8 Safe Operation Area

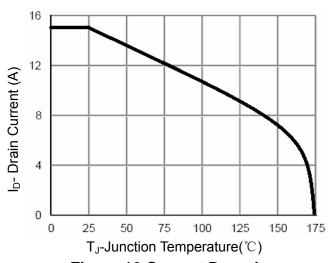
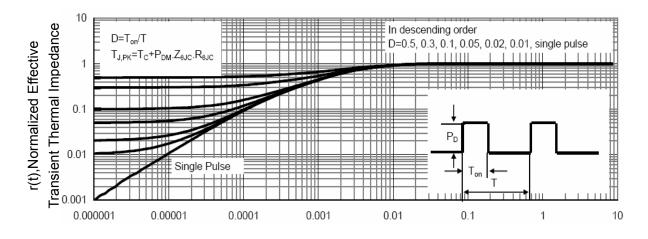


Figure 10 Current De-rating

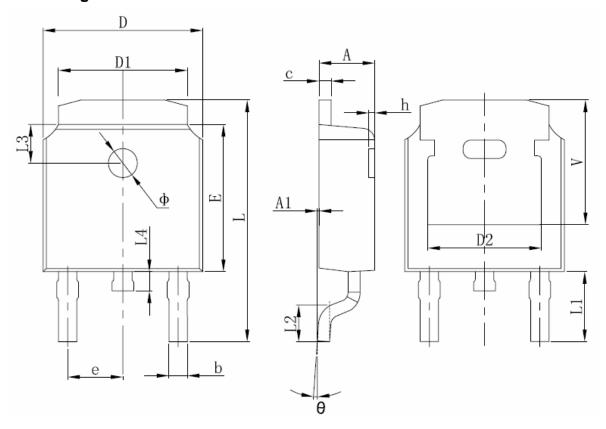


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Syllibol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830	REF.	0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900	REF.	0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600	REF.	0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		

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